2N5400







### **PNP General Purpose Amplifier**

This device is designed for use as general purpose amplifiers and switches requiring high voltages.

#### **Absolute Maximum Ratings\*** TA = 25°C unless otherwise noted

| Symbol                            | Parameter  | Value       | Units |
|-----------------------------------|--|-------------|-------|
| V <sub>CEO</sub>                  | Collector-Emitter Voltage                        | 120         | V     |
| V <sub>CBO</sub>                  | Collector-Base Voltage                           | 130         | V     |
| V <sub>EBO</sub>                  | Emitter-Base Voltage                             | 5.0         | V     |
| Ic                                | Collector Current - Continuous                   | 600         | mA    |
| T <sub>J</sub> , T <sub>stg</sub> | Operating and Storage Junction Temperature Range | -55 to +150 | °C    |

\*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES: 1) These ratings are based on a maximum junction temperature of 150 degrees C. 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

#### **Thermal Characte**

| rictice  |                                  |
|----------|----------------------------------|
| eristics | TA = 25°C unless otherwise noted |
|          |                                  |

| Symbol          | Characteristic                          | Max    | Units |
|-----------------|---|--------|-------|
|                 |   | 2N5400 |       |
| P <sub>D</sub>  | Total Device Dissipation                | 625    | mW    |
|                 | Derate above 25°C                       | 5.0    | mW/°C |
| $R_{\theta JC}$ | Thermal Resistance, Junction to Case    | 83.3   | °C/W  |
| $R_{\theta JA}$ | Thermal Resistance, Junction to Ambient | 200    | °C/W  |

## PNP General Purpose Amplifier (continued)

| Symbol  | Parameter   | Test Conditions   | Min            | Max                                    | Units       |
|---|---|---|----------------|--|-------------|
| OFF CHA   | ARACTERISTICS   |   |                |  |             |
| V <sub>(BR)CEO</sub>  | Collector-Emitter Breakdown Voltage*  | $I_{\rm C} = 1.0 \text{ mA}, I_{\rm B} = 0$   | 120            |  | V           |
| V <sub>(BR)CBO</sub>  | Collector-Base Breakdown Voltage  | $I_{\rm C} = 100 \ \mu {\rm A}, \ I_{\rm E} = 0$  | 130            |  | V           |
| V <sub>(BR)EBO</sub>  | Emitter-Base Breakdown Voltage  | $I_{\rm E} = 10 \ \mu A, \ I_{\rm C} = 0$   | 5.0            |  | V           |
| I <sub>CBO</sub>  | Collector Cutoff Current  | $V_{CB} = 100 \text{ V}, I_E = 0$<br>$V_{CB} = 100 \text{ V}, I_E = 0, T_A = 100 ^{\circ}\text{C}$  |                | 100<br>100                             | nA<br>μA    |
| I <sub>EBO</sub>  | Emitter Cutoff Current  | $V_{EB} = 3.0 \text{ V}, I_{C} = 0$   |                | 50                                     | nA          |
| h <sub>FE</sub>   | DC Current Gain   | $V_{CE} = 5.0 \text{ V}, I_C = 1.0 \text{ mA}$<br>$V_{CE} = 5.0 \text{ V}, I_C = 10 \text{ mA}$   | 30<br>40       | 180                                    |             |
| h <sub>FE</sub>   | DC Current Gain   | $V_{CE} = 5.0 \text{ V}, I_{C} = 1.0 \text{ mA}$  | 30             |  |             |
| h <sub>FE</sub>   | DC Current Gain   | $V_{CE} = 5.0 \text{ V}, I_{C} = 10 \text{ mA}$   | 30<br>40<br>40 | 180                                    |             |
|   | DC Current Gain<br>Collector-Emitter Saturation Voltage   |   | 40             | 180<br>0.2                             | V           |
| V <sub>CE(sat)</sub>  | Collector-Emitter Saturation Voltage  |   | 40             |  | V           |
| V <sub>CE(sat)</sub>  |   | $ \begin{array}{l} V_{CE} = 5.0 \ V, \ I_{C} = 10 \ mA \\ V_{CE} = 5.0 \ V, \ I_{C} = 50 \ mA \\ I_{C} = 10 \ mA, \ I_{B} = 1.0 \ mA \\ I_{C} = 50 \ mA, \ I_{B} = 5.0 \ mA \\ I_{C} = 10 \ mA, \ I_{B} = 1.0 \ mA \end{array} $  | 40             | 0.2<br>0.5<br>1.0                      | V<br>V      |
| V <sub>CE(sat)</sub>  | Collector-Emitter Saturation Voltage  |   | 40             | 0.2<br>0.5                             | V           |
| V <sub>CE(sat)</sub><br>V <sub>BE(sat)</sub><br>SMALL S   | Collector-Emitter Saturation Voltage<br>Base-Emitter Saturation Voltage   | $V_{CE} = 5.0 \text{ V}, I_{C} = 10 \text{ mA}$ $V_{CE} = 5.0 \text{ V}, I_{C} = 50 \text{ mA}$ $I_{C} = 10 \text{ mA}, I_{B} = 1.0 \text{ mA}$ $I_{C} = 50 \text{ mA}, I_{B} = 5.0 \text{ mA}$ $I_{C} = 10 \text{ mA}, I_{B} = 1.0 \text{ mA}$ $I_{C} = 50 \text{ mA}, I_{B} = 5.0 \text{ mA}$ | 40             | 0.2<br>0.5<br>1.0<br>1.0               | V<br>V<br>V |
| V <sub>CE(sat)</sub><br>V <sub>BE(sat)</sub><br>SMALL S<br>C <sub>ob</sub>  | Collector-Emitter Saturation Voltage<br>Base-Emitter Saturation Voltage   | $\begin{split} V_{CE} &= 5.0 \text{ V},        $  | 40<br>40       | 0.2<br>0.5<br>1.0<br>1.0<br>6.0        | V<br>V      |
| V <sub>CE(sat)</sub><br>V <sub>BE(sat)</sub><br>SMALL S<br>C <sub>ob</sub>  | Collector-Emitter Saturation Voltage<br>Base-Emitter Saturation Voltage<br>SIGNAL CHARACTERISTICS<br>Output Capacitance<br>Current Gain - Bandwidth Product | $\begin{split} V_{CB} &= 5.0 \text{ V},        $  | 40             | 0.2<br>0.5<br>1.0<br>1.0<br>6.0<br>400 | V<br>V<br>V |
| $\begin{array}{c} h_{FE} \\ \hline V_{CE(sat)} \\ \hline V_{BE(sat)} \\ \hline \\ \hline \\ SMALL S \\ \hline \\ \hline \\ C_{ob} \\ \hline \\ f_T \\ \hline \\ \hline \\ h_{fe} \\ \hline \end{array}$ | Collector-Emitter Saturation Voltage<br>Base-Emitter Saturation Voltage   | $\begin{split} V_{CE} &= 5.0 \text{ V},        $  | 40<br>40       | 0.2<br>0.5<br>1.0<br>1.0<br>6.0        | V<br>V<br>V |

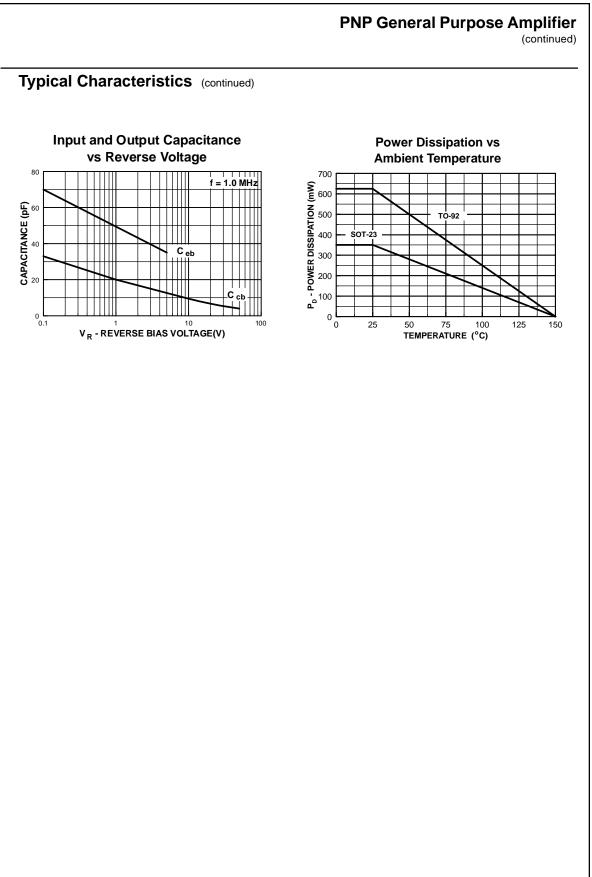
\*Pulse Test: Pulse Width  $\pm$  300 ms, Duty Cycle  $\pm$  2.0%

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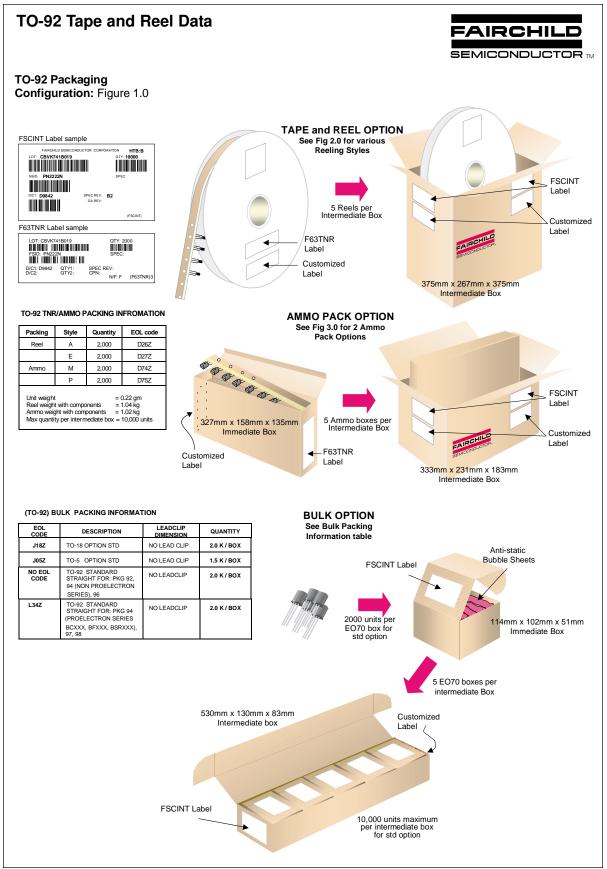
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**PNP General Purpose Amplifier** 

#### (continued) **Typical Characteristics Typical Pulsed Current Gain Collector-Emitter Saturation** vs Collector Current Voltage vs Collector Current / \_ \_ \_ \_ 5V / <sub>CE</sub> = 5V β = 10 Π 125 °d 25 °C 25 0 125 °C °C ||| 0 L 0.1 0.0001 0.001 0.01 0.1 I c - COLLECTOR CURRENT (A) 10 100 I c - COLLECTOR CURRENT (mA) **Base-Emitter Saturation** Base-Emitter ON Voltage vs **Collector Current** Voltage vs Collector Current V BASE-EMITTER VOLTAGE (V) 0.0 0.0 0.1 0.0 0.1 0.1 0°C Ш Ш 25 °C 125 °C 125 °C β = 10 10 100 10 100 1 1 I c - COLLECTOR CURRENT (mA) Ic - COLLECTOR CURRENT (mA) **Collector-Emitter Breakdown Collector-Cutoff Current** vs Ambient Temperature Voltage with Resistance I<sub>ceo</sub>- collector current (nA) 0 1 0 0 0 **Between Emitter-Base** V<sub>CB</sub> = 100V 25 50 75 100 125 150 10 RESISTANCE (kΩ) 100 1000 T<sub>A</sub> - AM BIENT TE MPE RATURE (°C)

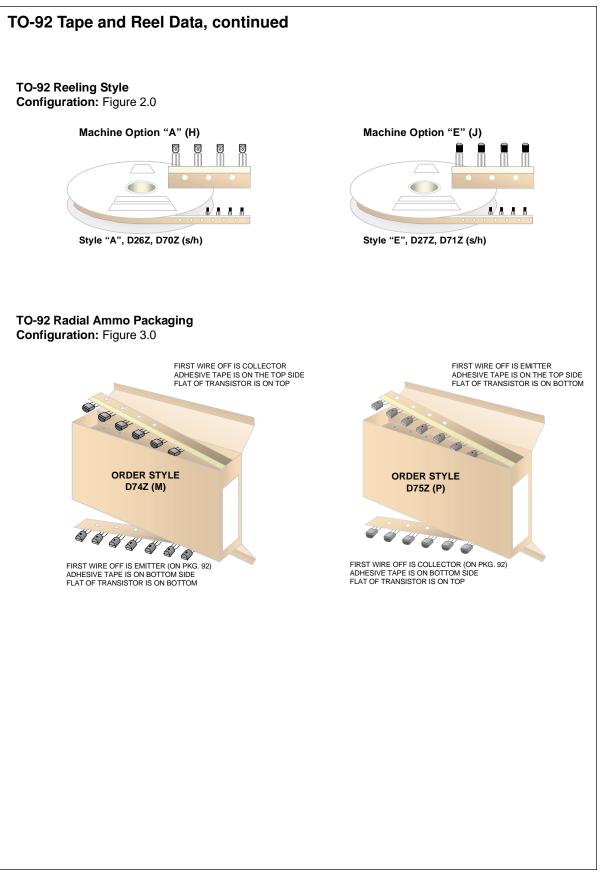


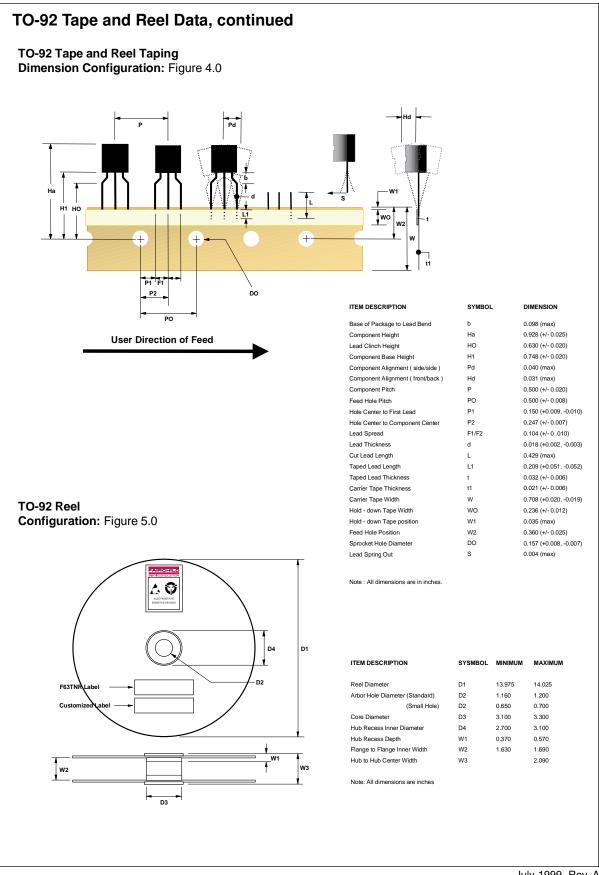
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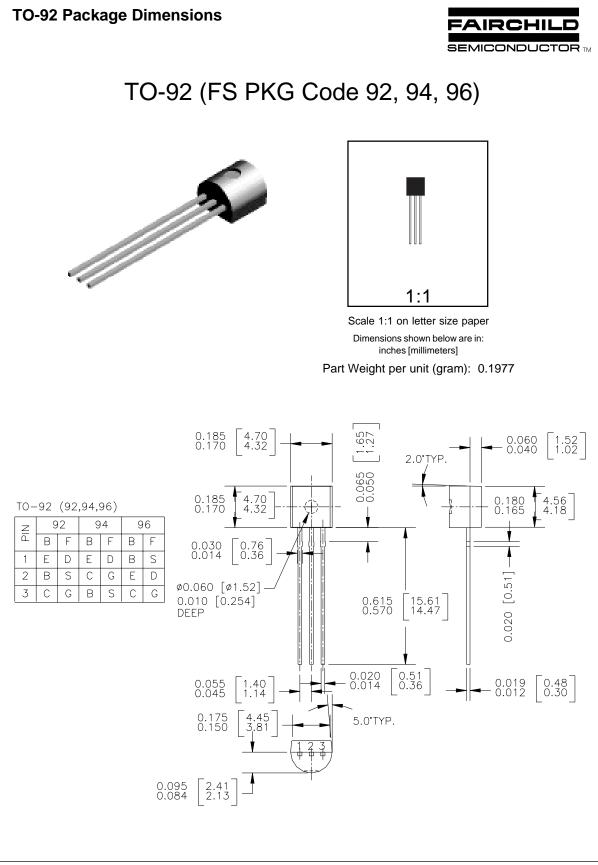
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March 2001, Rev. B1





July 1999, Rev. A



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